

Pil Ju Ko

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Dual-Gate Graphene/h-BN/GaSe Metal-Insulator-Semiconductor Field-Effect Transistor (MISFET). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2022, 219, .	1.8	2
2	Black Phosphorus/Molybdenum Diselenide Heterojunction-Based Photodetector. <i>Journal of Electronic Materials</i> , 2021, 50, 5713-5720.	2.2	5
3	Tunable optoelectronic properties of a two-dimensional graphene/In ₂ Se ₃ /graphene-based ferroelectric semiconductor field-effect transistor. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 20252-20258.	2.2	8
4	Photovoltaic Characteristics of GaSe/MoSe ₂ Heterojunction Devices. <i>Nanoscale Research Letters</i> , 2021, 16, 171.	5.7	6
5	Optoelectronic properties of two-dimensional molybdenum diselenide dual-gated MISFET-based photodetector. <i>Optik</i> , 2020, 224, 165427.	2.9	3
6	Thickness Dependence of Optoelectronic Properties of Molybdenum Diselenide-Based Nanodevices. <i>Journal of Electronic Materials</i> , 2019, 48, 7025-7030.	2.2	5
7	Micro-Hall Sensors Based on Two-Dimensional Molybdenum Diselenide. <i>Journal of Nanoscience and Nanotechnology</i> , 2019, 19, 4330-4332.	0.9	3
8	Effects of Rapid Thermal Treatment on Characteristics of Magnetron-Sputtered NiO Thin Films for Supercapacitor Applications. <i>Journal of Nanoscience and Nanotechnology</i> , 2018, 18, 6213-6219.	0.9	7
9	High-performance near-infrared photodetector based on nano-layered MoSe ₂ . <i>Semiconductor Science and Technology</i> , 2017, 32, 065015.	2.0	46
10	Green synthesis of reduced graphene oxide/Fe ₃ O ₄ /Ag ternary nanohybrid and its application as magnetically recoverable catalyst in the reduction of 4-nitrophenol. <i>Applied Organometallic Chemistry</i> , 2017, 31, e3781.	3.5	27
11	Rapid laser annealing of Cu(In,Ga)Se ₂ thin films by using a continuous wave Nd:YAG laser ($\lambda = 532$ nm). <i>Journal of the Korean Physical Society</i> , 2017, 70, 809-815.	0.7	3
12	Cu(In,Ga)Se ₂ thin films annealed using a continuous wave Nd:YAG laser ($\lambda = 532$ nm): Effects of laser-annealing time. <i>Journal of the Korean Physical Society</i> , 2017, 71, 1038-1047.	0.7	2
13	Gate-tunable optoelectronic properties of a nano-layered GaSe photodetector. <i>Optical Materials Express</i> , 2017, 7, 587.	3.0	18
14	Deviations from stoichiometry and molecularity in non-stoichiometric Ag-In-Se thin films: Effects on the optical and the electrical properties. <i>Journal of the Korean Physical Society</i> , 2016, 69, 1817-1823.	0.7	1
15	Thickness dependence on the optoelectronic properties of multilayered GaSe based photodetector. <i>Nanotechnology</i> , 2016, 27, 325202.	2.6	34
16	Multifunctional WSe ₂ /SnSe ₂ /WSe ₂ van der Waals heterostructures. <i>Journal of Materials Science: Materials in Electronics</i> , 0, , 1.	2.2	2